

## NCE N-Channel Enhancement Mode Power MOSFET

### Description

The NCE3090K uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

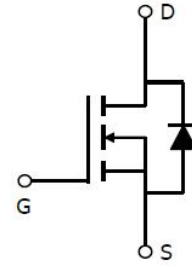
### General Features

- $V_{DS} = 30V, I_D = 90A$   
 $R_{DS(ON)} = 3.4m\Omega$  (typical) @  $V_{GS} = 10V$   
 $R_{DS(ON)} = 6.9m\Omega$  (typical) @  $V_{GS} = 4.5V$
- High density cell design for ultra low  $R_{dson}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high  $E_{AS}$
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

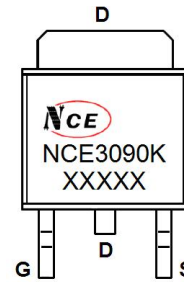
### Application

- DC/DC converters
- Synchronous Rectifier

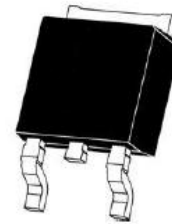
**100% UIS TESTED!**



Schematic diagram



Marking and pin assignment



TO-252-2L top view

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE3090K	NCE3090K	TO-252-2L	Ø330mm	12mm	2500 units

### Absolute Maximum Ratings ( $T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	90	A
Drain Current-Continuous( $T_C = 100^\circ C$ )	$I_D(100^\circ C)$	63.6	A
Pulsed Drain Current (Note 1)	$I_{DM}$	200	A
Maximum Power Dissipation	$P_D$	105	W
Derating factor		0.7	W/ $^\circ C$
Single pulse avalanche energy (Note 5)	$E_{AS}$	380	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	$^\circ C$

### Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 2)	$R_{\theta JC}$	1.43	$^\circ C/W$
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## Electrical Characteristics (T<sub>c</sub>=25°C unless otherwise noted)

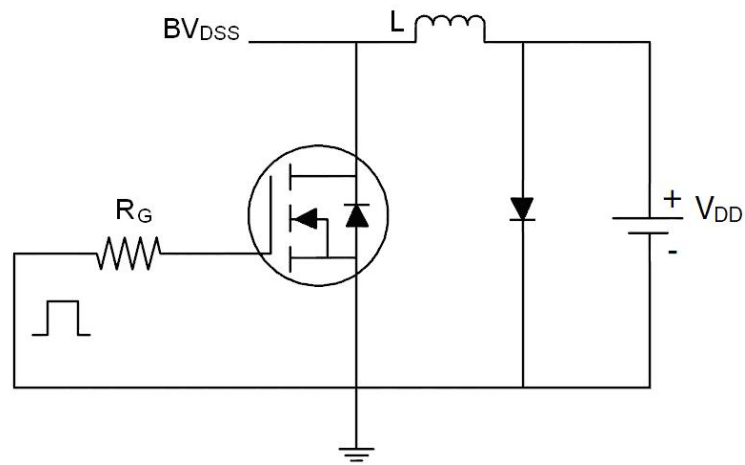
Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	30	38	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
<b>On Characteristics</b> (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1	1.7	2.5	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	-	3.4	4.2	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A		6.9	9.5	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =20A	20	-	-	S
<b>Dynamic Characteristics</b> (Note 4)						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, F=1.0MHz	-	3568	-	PF
Output Capacitance	C <sub>oss</sub>		-	422	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	341	-	PF
<b>Switching Characteristics</b> (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =15V, I <sub>D</sub> =20A V <sub>GS</sub> =10V, R <sub>GEN</sub> =3Ω	-	12	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	15	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	40	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	14	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =15V, I <sub>D</sub> =45A, V <sub>GS</sub> =10V	-	67	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	13.7	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	10.3	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =20A	-	-	1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	90	A
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> = 20A di/dt = 100A/μs (Note 3)	-	29	-	nS
Reverse Recovery Charge	Q <sub>rr</sub>		-	32	-	nC

### Notes:

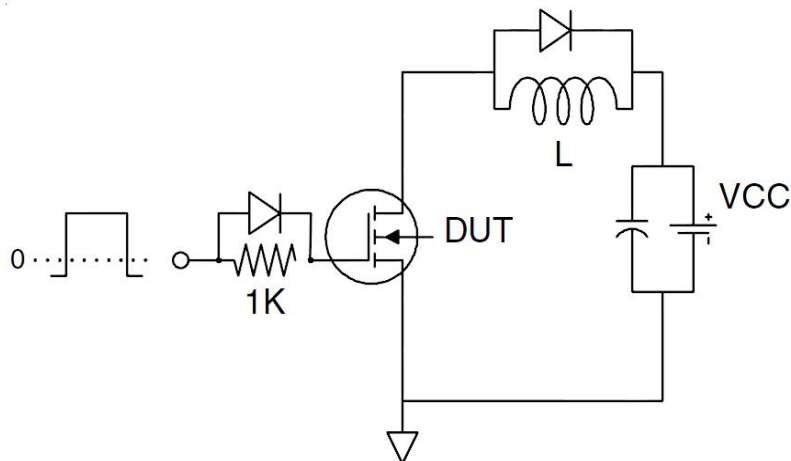
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition: T<sub>J</sub>=25°C, V<sub>DD</sub>=15V, V<sub>G</sub>=10V, L=0.5mH, R<sub>G</sub>=25Ω;

## Test Circuit

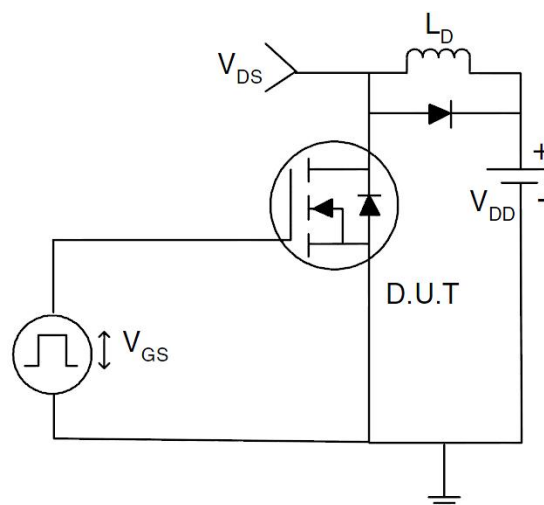
### 1) E<sub>AS</sub> Test Circuit



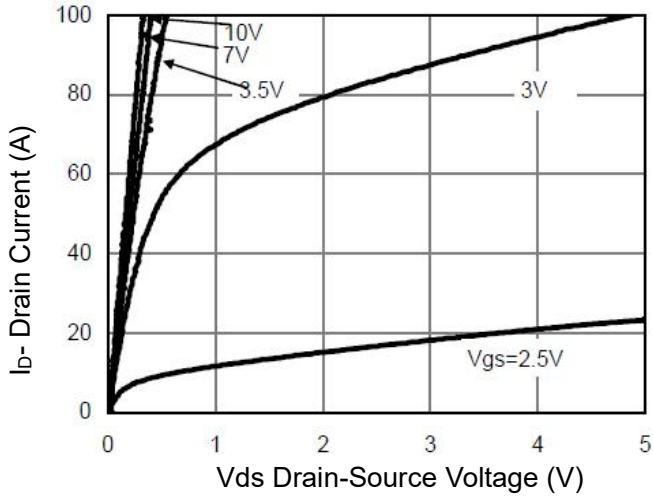
### 2) Gate Charge Test Circuit



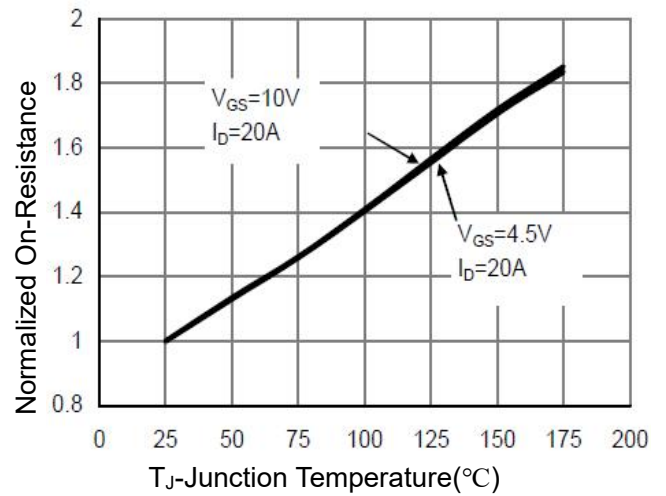
### 3) Switch Time Test Circuit



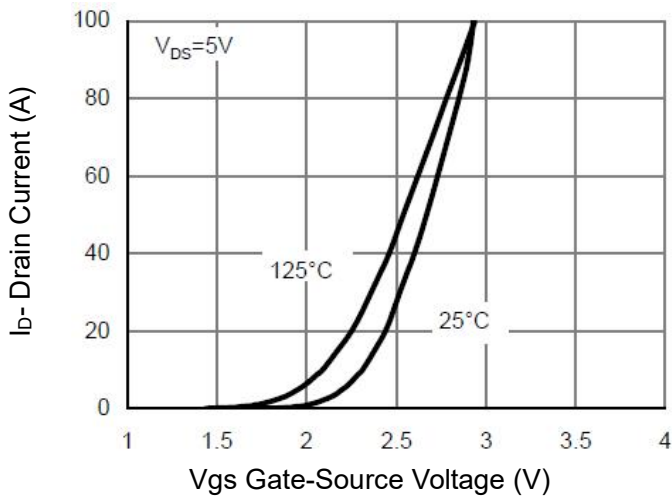
**Typical Electrical and Thermal Characteristics (Curves)**



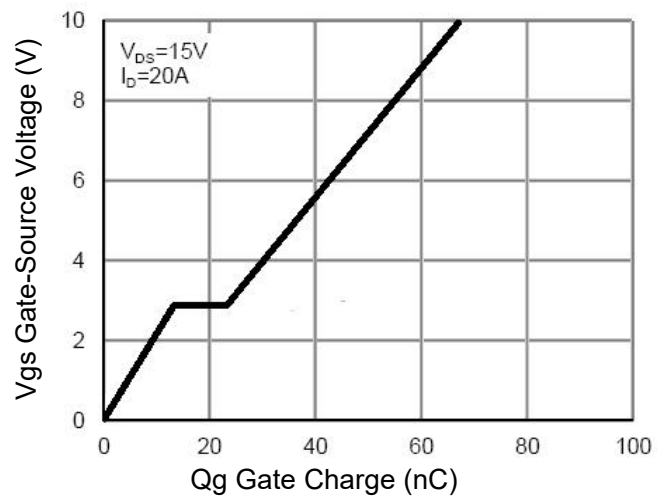
**Figure 1 Output Characteristics**



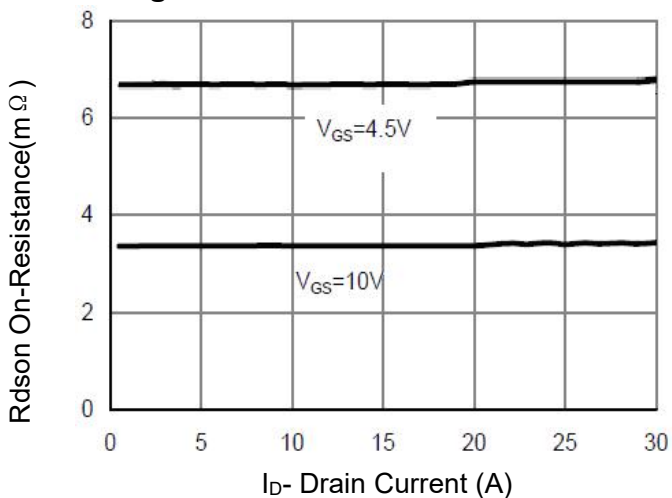
**Figure 4  $R_{dson}$ -Junction Temperature**



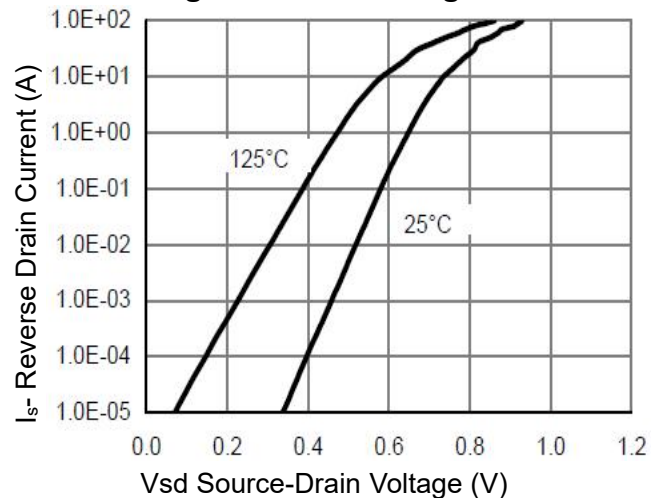
**Figure 2 Transfer Characteristics**



**Figure 5 Gate Charge**



**Figure 3  $R_{dson}$ - Drain Current**



**Figure 6 Source- Drain Diode Forward**

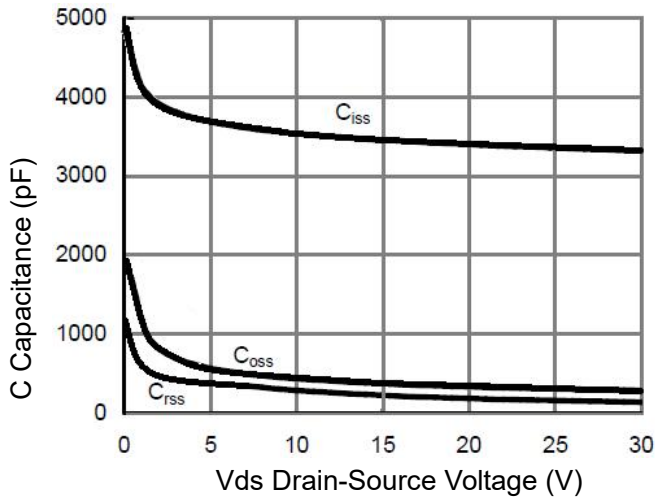


Figure 7 Capacitance vs Vds

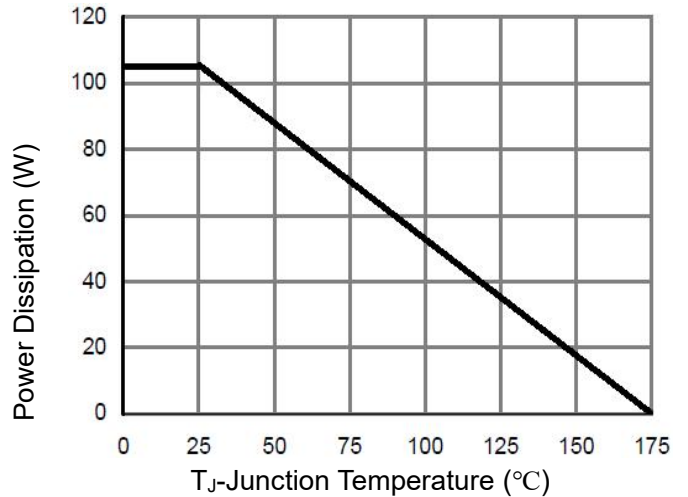


Figure 9 Power De-rating

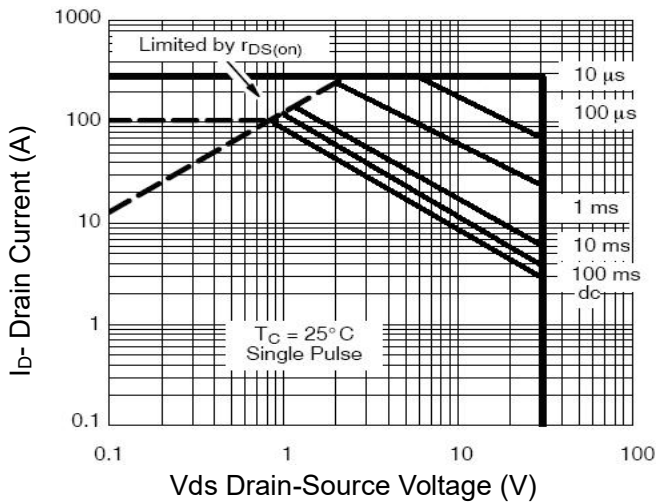


Figure 8 Safe Operation Area

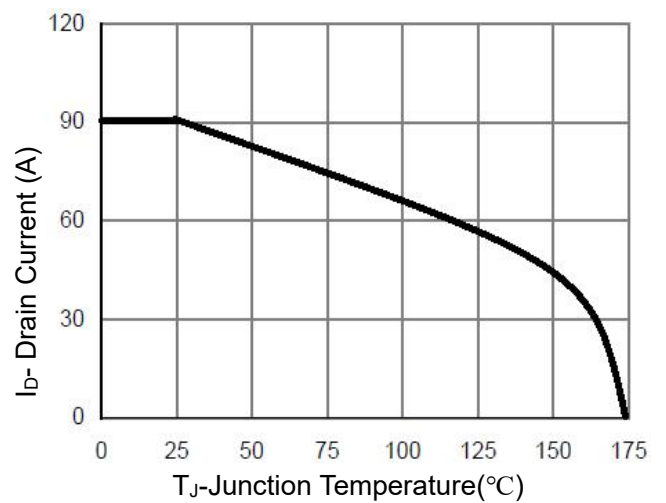


Figure 10 ID Current Derating

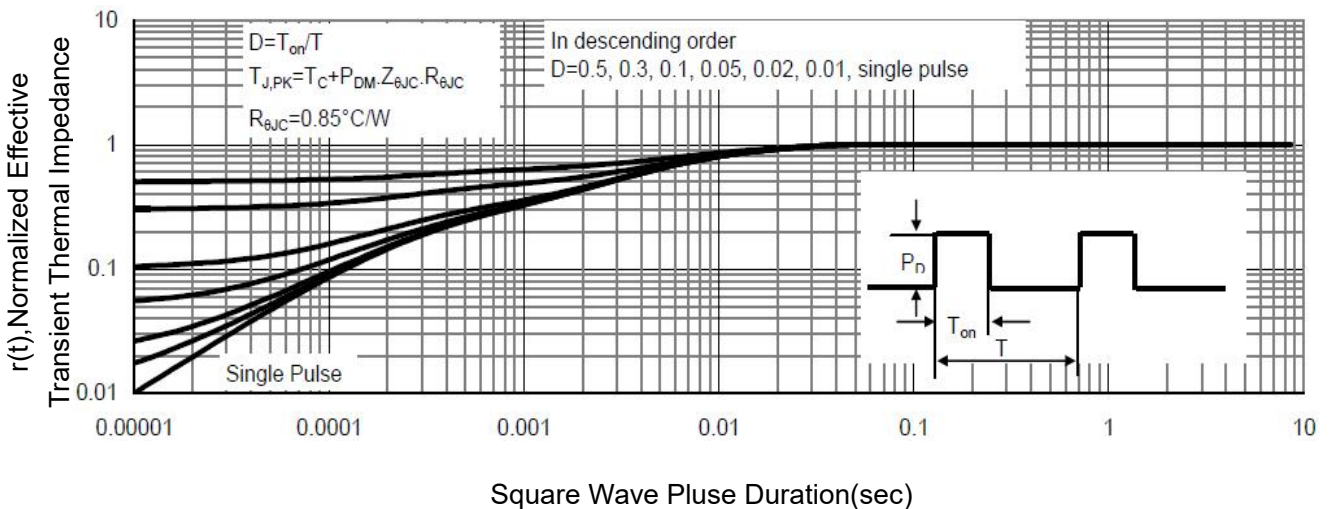
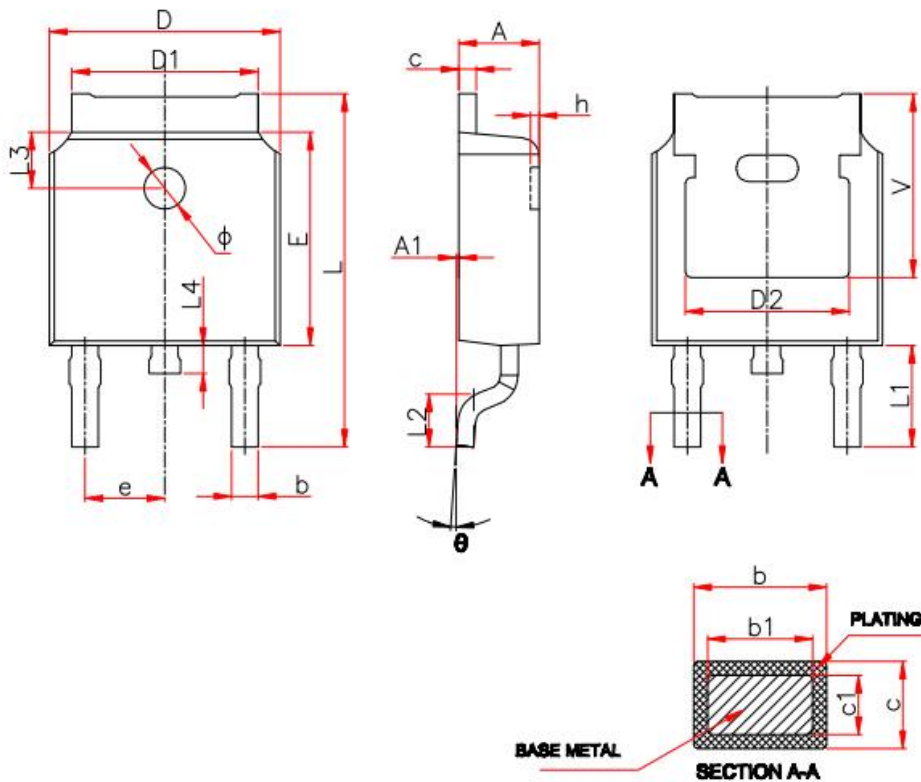


Figure 11 Normalized Maximum Transient Thermal Impedance

## TO-252 Package Information



Symbol	Millimeters	
	Min.	Max.
A	2.20	2.40
A1	0.00	0.13
b	0.66	0.86
b1	0.73	0.79
c	0.46	0.58
c1	0.50	0.52
D	6.50	6.70
D1	5.10	5.46
D2	4.83 REF.	
E	6.00	6.20
e	2.19	2.39
L	9.80	10.40
L1	2.90 REF.	
L2	1.40	1.70
L3	1.60 REF.	
L4	0.60	1.00
Φ	1.10	1.30
θ	0°	8°

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